

REMARKS

This submission is in response to the Office Action dated April 2, 2008 (the "Office Action"). Claims 1– 27 are pending in the application. Applicants have amended claims 1, 2, 5, 8, 9, 10, 17, 18, 19, 20, 21, 23 and 25 without prejudice or disclaimer. No new matter has been added.

Interview Summary

Applicant appreciates the courtesy granted to Applicant's attorney, Michael A. Scaturro (Reg. No. 51,356) during a telephonic interview conducted on August 20, 2008. During the telephonic interview, Applicant's attorney discussed certain structural differences between the Field Effect Transistor (FET) taught in Hebiguchi with the Field Effect Transistor of the invention. The Examiner's Supervisor indicated that while Hebiguchi is structurally different from the invention, these differences were not presently found in the claim language necessitating certain amendments without introducing new matter.

Claim Objections

Claim 8 was objected to under 37 CFR 1.75(c) as being in improper form because a multiple dependent claim cannot depend from another multiple dependent claim. Claim 8 has been amended in a manner which is believed to overcome the objection.

Claim 23 was objected to under 37 CFR 1.75(c) as being in improper form because a multiple dependent claim does not refer back in the alternative only. Claim 23 has been amended in a manner which is believed to overcome the objection.

Claim Rejections

Claim 21 was rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as his invention. Claims 20 and 21 have been amended in a manner which is believed to overcome the objection.

102 Rejections

The Examiner has rejected claims 1-7, 9-22, 24-27 in the Office Action, under 35 U.S.C. § 102(b), as being anticipated by U.S. Patent No. 5,801,398 ("Hebiguchi"). Applicants respectfully traverse the rejections. However, independent Claim 1 has been amended herein to better define Applicant's invention over Hebiguchi. Claim 1 now recites limitations and/or features, which are not disclosed by Hebiguchi. It is respectfully submitted that the cited portions of Hebiguchi fail to disclose or suggest the specific combination of claim 1 as amended. For example, the cited portions of Hebiguchi do not disclose wherein the gate electrode and source electrode are arranged in an wholly opposed laterally overlapping relationship to each other, the source electrode and gate electrode being centrally located above the semiconductor body, as in amended claim 1. In contrast to claim 1, Hebiguchi discloses *a source electrode 45 and a drain electrode 46 formed opposed to each other on the right and left sides in such a manner as*

to cover the right and left end portions (shown in FIG. 1) of the semiconductor active film

44. See Hebiguchi, col. 6, lines 25 – 35. In further contrast to claim 1, Hebiguchi discloses where the source and gate electrodes only tangentially overlap. See Hebiguchi, Fig. 1 where a small tangential portion of source electrode 45 overlaps gate electrode 42. It is respectfully submitted that a gate electrode and source electrode arranged in a wholly opposed laterally overlapping relationship to each other, where the gate and source electrodes are both centrally located above the semiconductor body, is different from a source electrode formed on the right end portion of the semiconductor active film only tangentially overlapping the gate electrode. Therefore, claim 1 is believed to be allowable.

Claims 3-11 and 13-16 depend from claim 1, which Applicants have shown to be allowable. Hence, Hebiguchi fails to disclose at least one element of claims 3-11 and 13-16. Accordingly, claims 3-11 and 13-16 are also allowable, at least by virtue of their dependence from claim 1.

Independent Claims 2, 17, 18, 19, 25 and 26 recite similar subject matter as Claim 1 and contain the limitations of Claim 1. Hence, for at least the same reasons given for Claim 1, withdrawal of the rejection under 35 U.S.C. §102(b) with respect to Claims 2, 17, 18, 19, 25 and 26 and allowance thereof is respectfully requested.

Claims 20-24 depend from claim 19, which Applicants have shown to be allowable. Hence, Hebiguchi fails to disclose at least one element of claims 20-24.

Accordingly, claims 20-24 are also allowable, at least by virtue of their dependence from claim 19.

CONCLUSION

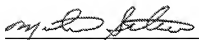
Applicants have pointed out specific features of the claims not disclosed, suggested, or rendered obvious by the cited portions of the cited references as applied in the Office Action. Accordingly, Applicants respectfully request reconsideration and withdrawal of each of the objections and rejections, as well as an indication of the allowability of each of the pending claims.

Any changes to the claims in this response, which have not been specifically noted to overcome a rejection based upon the prior art, should be considered to have been made for a purpose unrelated to patentability, and no estoppel should be deemed to attach thereto.

In view of the foregoing amendments and remarks, it is respectfully submitted that all claims presently pending in the application, namely, Claims 1-23 are believed to be in condition for allowance and patentably distinguishable over the art of record.

The Examiner is invited to contact Mr. Michael Scaturro, Philips Intellectual Counsel, Philips Electronics North America, at 516-414-2007 if such a call would facilitate allowance of this application.

Respectfully submitted,

A handwritten signature in black ink, appearing to read 'Michael A. Scaturro', is written over a horizontal line.

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